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(12) **United States Design Patent**
Matsumoto et al.

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(54) **BAFFLE PLATE FOR MANUFACTURING SEMICONDUCTOR**

(75) Inventors: **Naoki Matsumoto**, Sendai (JP); **Jun Yoshikawa**, Sendai (JP)

(73) Assignee: **Tokyo Electron Limited**, Tokyo (JP)

(**) Term: **14 Years**

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(30) **Foreign Application Priority Data**

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(51) **LOC (9) Cl.** **15-99**

(52) **U.S. Cl.**
USPC **D15/144**; D15/138

(58) **Field of Classification Search**
USPC D13/182; D15/138, 144, 199; 118/723;
156/345, 345.36, 345.41, 345.48;
204/298.06, 298.08, 298.11, 298.34;
336/232

See application file for complete search history.

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Primary Examiner — Patricia Palasik

(74) *Attorney, Agent, or Firm* — Leydig, Voit & Mayer Ltd.

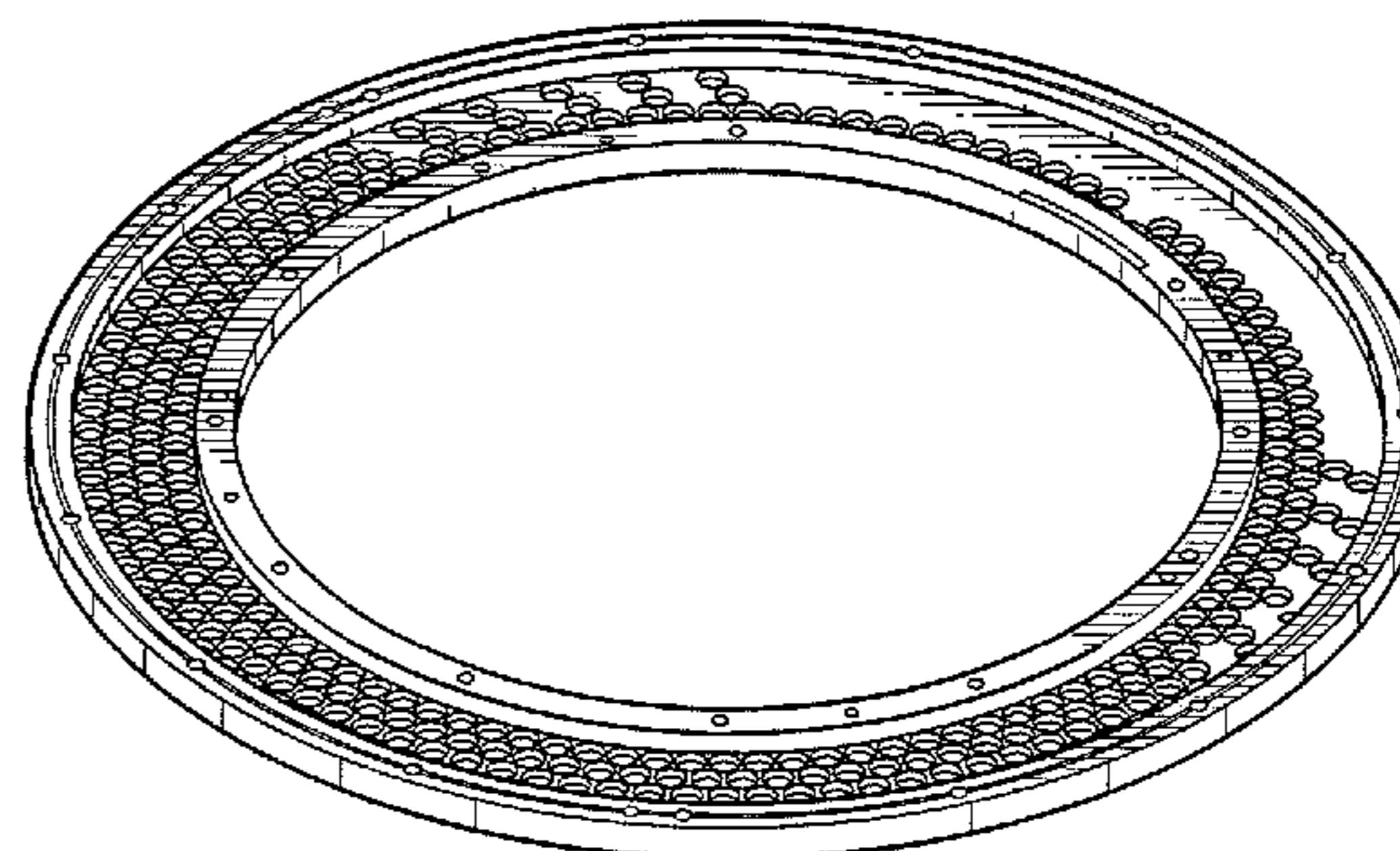
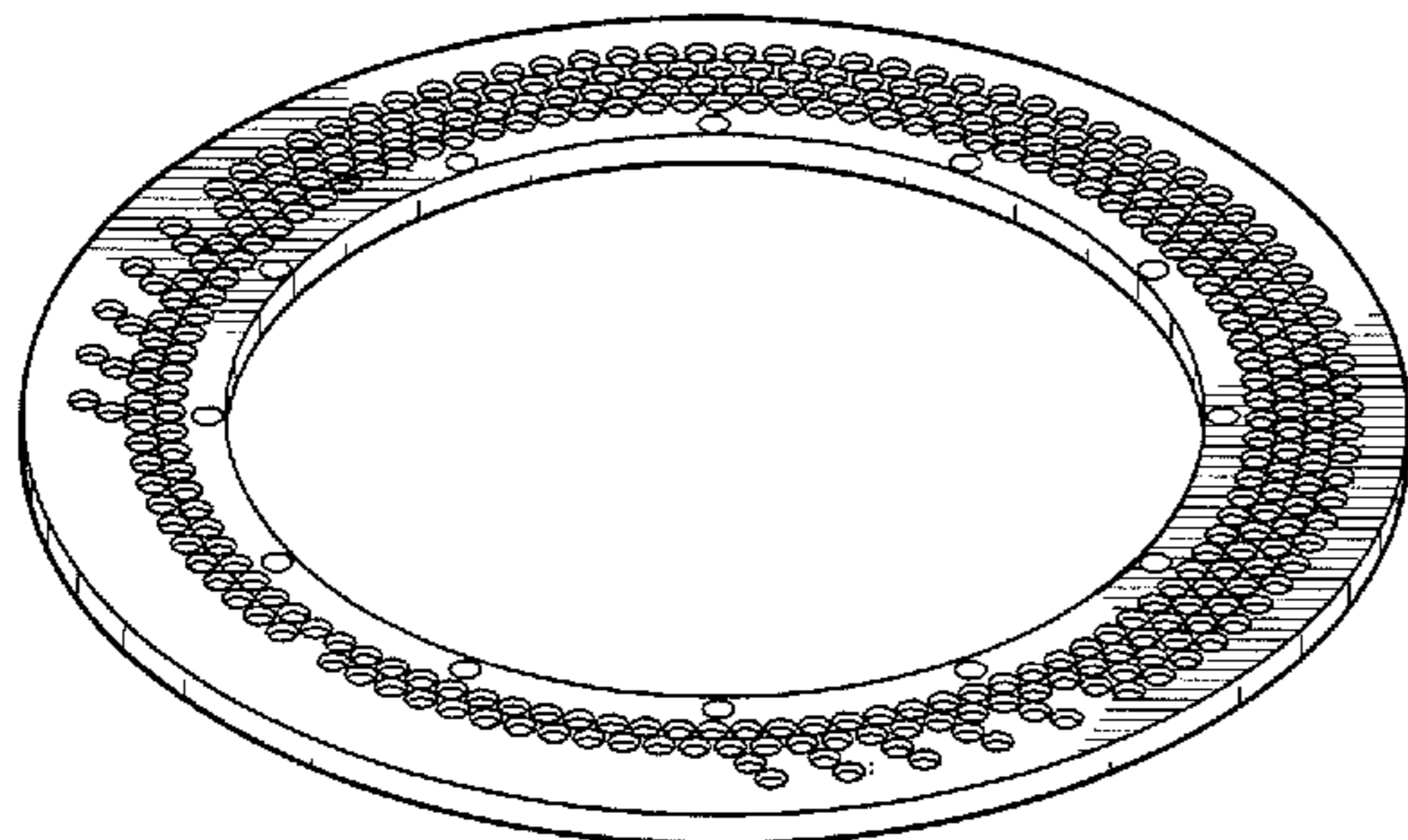
(57) **CLAIM**

The ornamental design for a baffle plate for manufacturing semiconductor, as shown and described.

DESCRIPTION

FIG. 1 is a front view of a baffle plate of the present invention. FIG. 2 is a rear view of the baffle plate of FIG. 1. FIG. 3 is a top plan view of the baffle plate of FIG. 1. FIG. 4 is a bottom view of the baffle plate of FIG. 1. FIG. 5 is a right side view of the baffle plate of FIG. 1. FIG. 6 is a left view of the baffle plate of FIG. 1. FIG. 7 is a first perspective view of the baffle plate of FIG. 1. FIG. 8 is a second perspective view of the baffle plate of FIG. 1; and, FIG. 9 is a view of the baffle plate of FIG. 1 in use, wherein, for example, in a plasma processing device, gas entering a chamber is ionized, and a wafer is treated by an etching process with ions, and gas is exhausted from the chamber. The features shown in broken lines depict environmental subject matter only and form no part of the claimed design.

1 Claim, 4 Drawing Sheets



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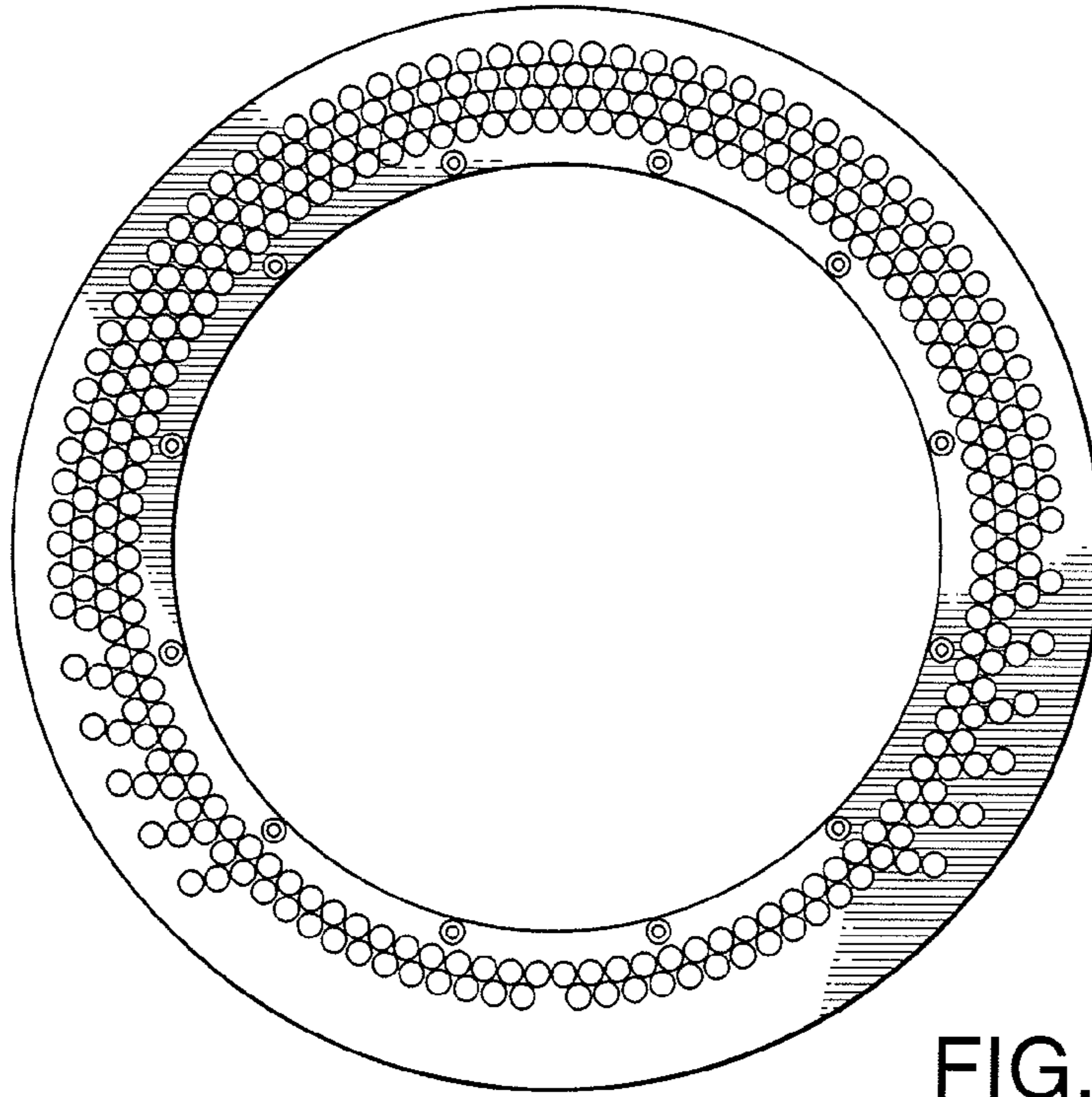


FIG. 1

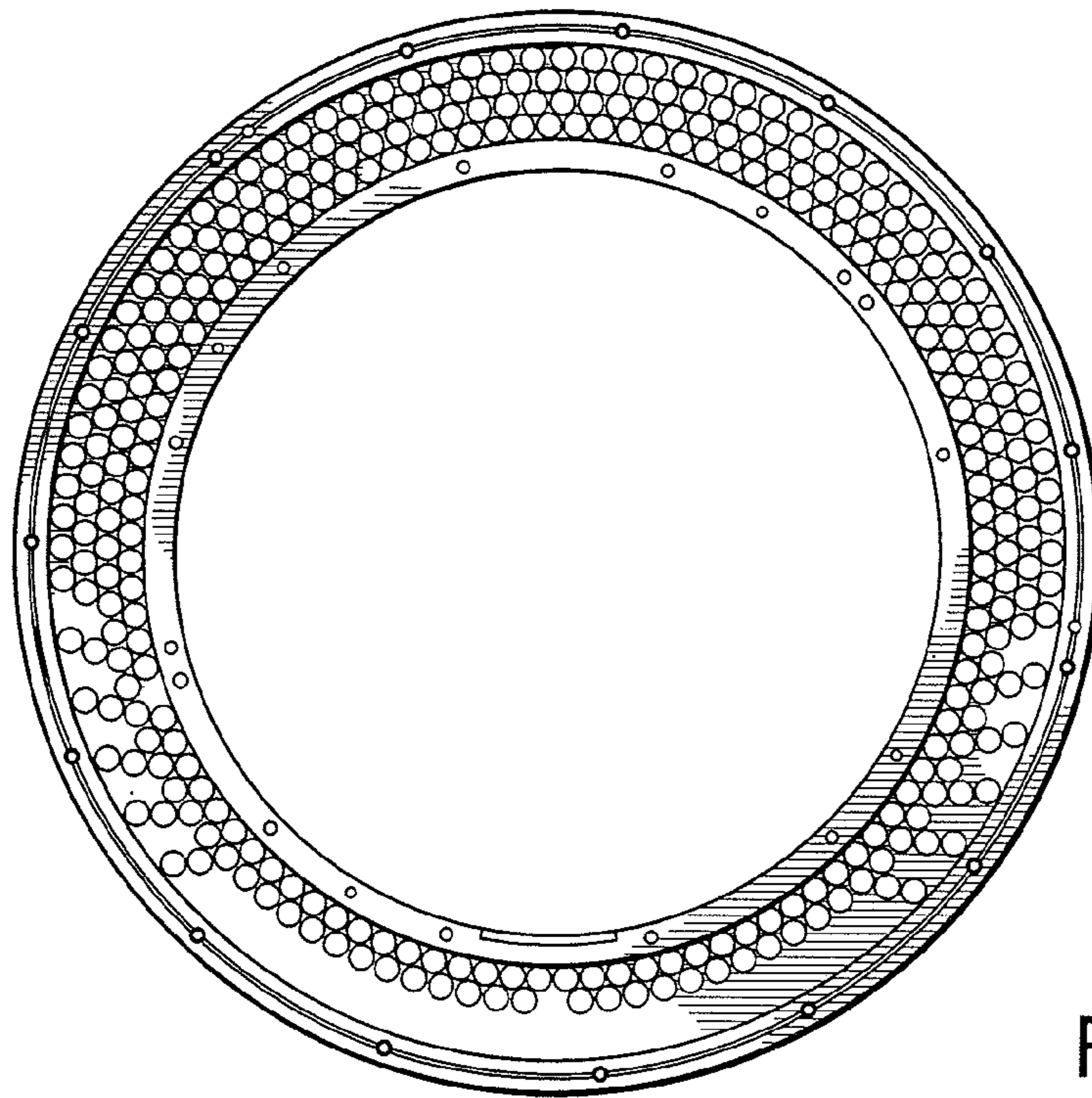


FIG. 2

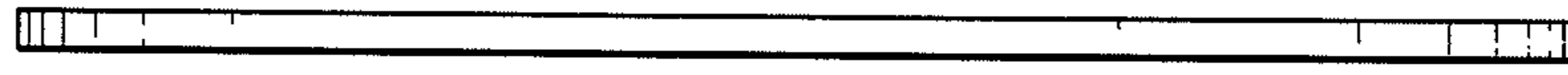


FIG. 3

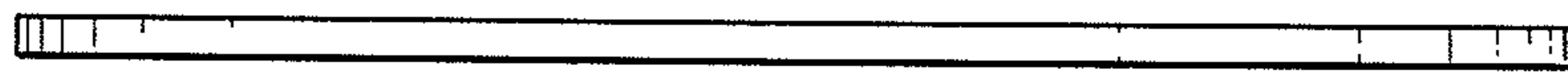


FIG. 4



FIG. 5



FIG. 6

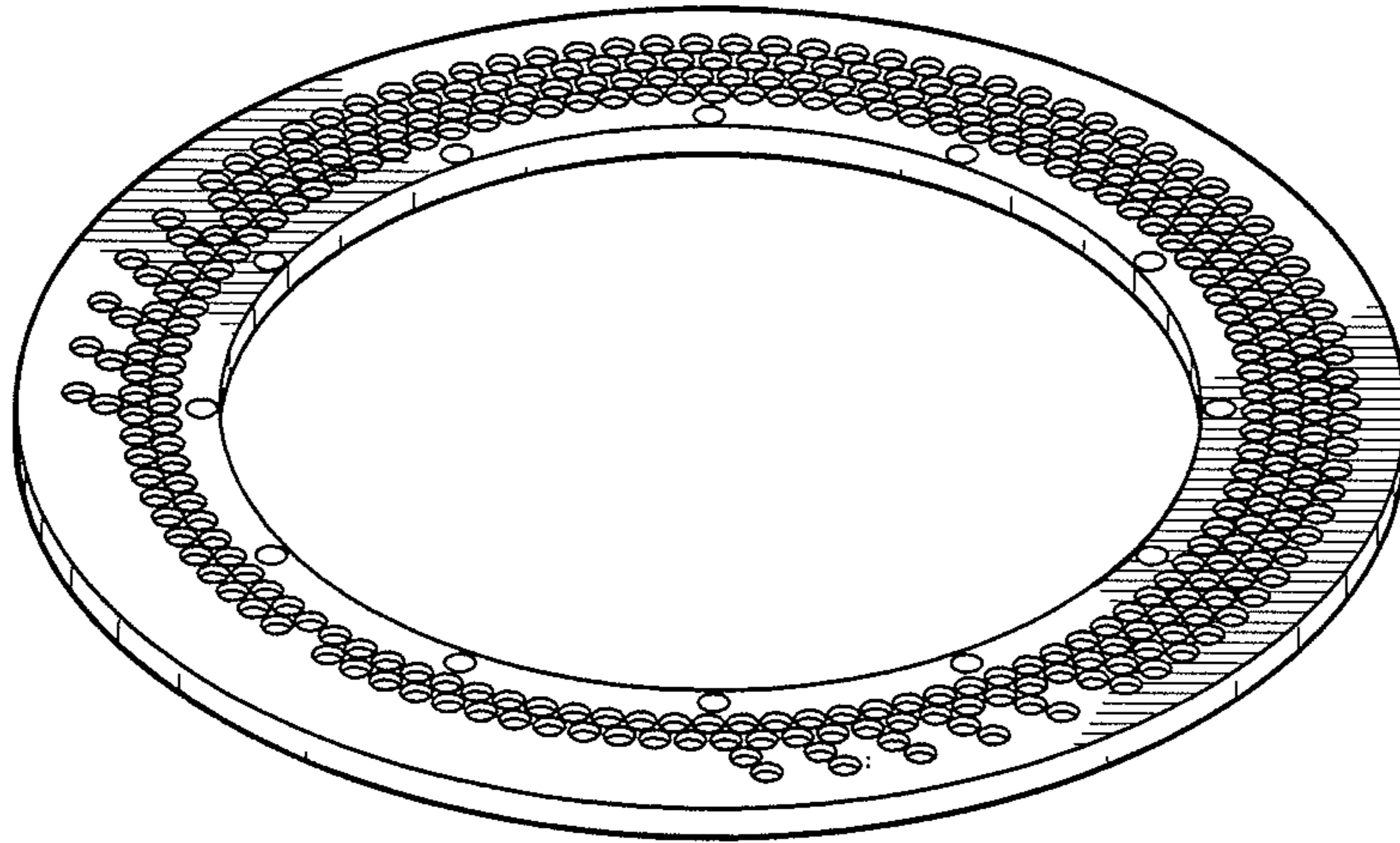


FIG. 7

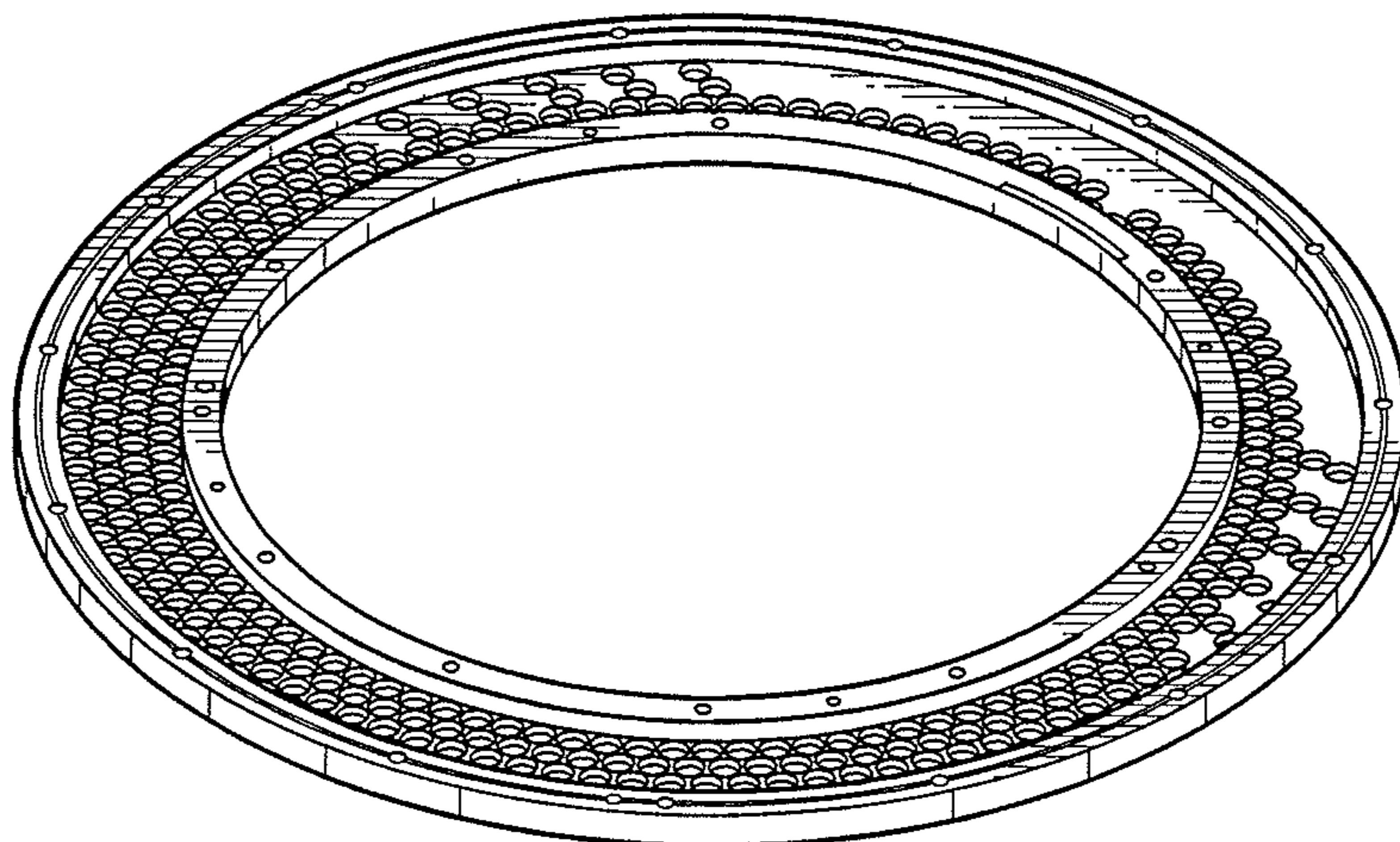


FIG. 8

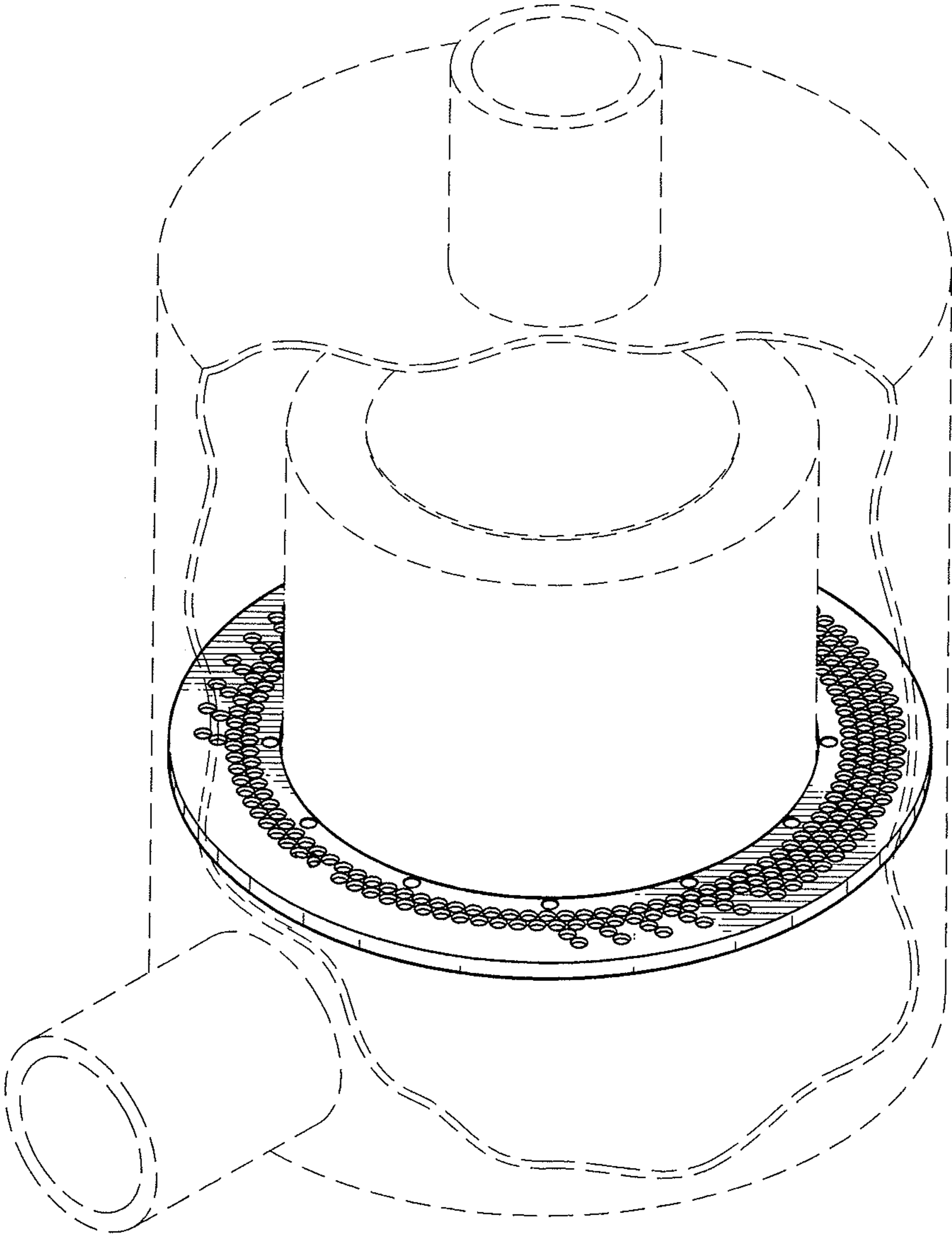


FIG. 9